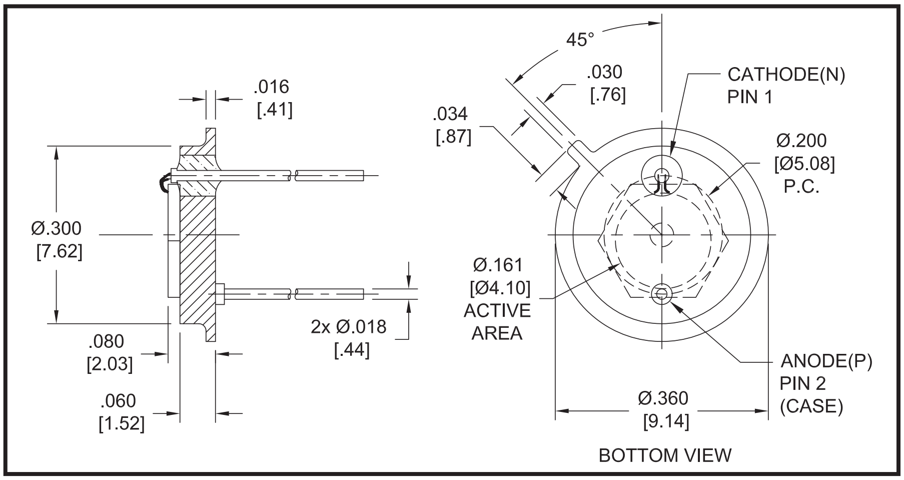
PHOTODIODE 13 mm^2

UVG12



FEATURES

- Circular active area
- Ideal for 193-400 nm detection
- 100% internal QE
- No cap for maximum responsivity
- Sacrificial cap taped on for shipping purposes

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

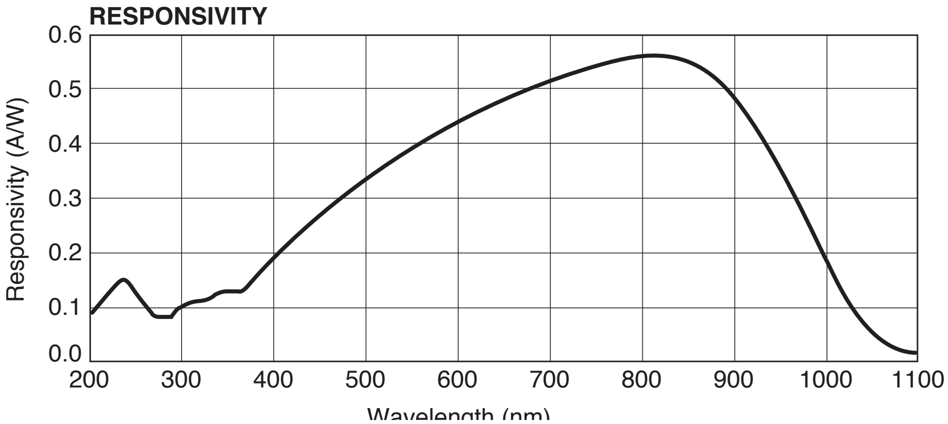
PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	Ø 4.1 mm		13.2		mm^2
Responsivity, $\mathcal{R}$	@ 254 nm	0.105	0.115	0.125	A/W
Shunt Resistance	$V_F = \pm 10$ mV	100	1000		Mohm
Reverse Breakdown Voltage, V_R	$I_R = 1\ \mu$A		9		Volts
Capacitance, C	$V_R = 0$ V		3	7	nF
Rise Time	$V_R = 0$ V			4	μsec

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Storage Temperature Range	-20° TO 80°C
Maximum Junction Temperature	80°C
Lead Soldering Temperature[1]	240°C

[1] 0.0625" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode “Handling Precautions for IRD Detectors” prior to removing cover.



RESPONSIVITY
Responsivity (A/W)
0.0
0.1
0.2
0.3
0.4
0.5
0.6
200
300
400
500
600
700
800
900
1000
1100
Wavelength (nm)